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December 2012

FDS6699S
30V N-Channel PowerTrench® SyncFET™

Features

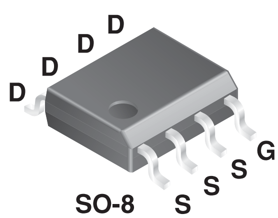
- 21 A, 30 V Max $R_{DS(ON)}$ = 3.6 mΩ @ V_{GS} = 10 V
  Max $R_{DS(ON)}$ = 4.5 mΩ @ V_{GS} = 4.5 V
- Includes SyncFET Schottky body diode
- High performance trench technology for extremely low $R_{DS(ON)}$ and fast switching
- High power and current handling capability
- 100% R_G (Gate Resistance) tested

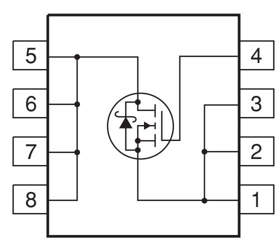
Applications

- Synchronous Rectifier for DC/DC Converters –
  - Notebook Vcore low side switch
  - Point of Load low side switch

General Description

The FDS6699S is designed to replace a single SO-8 MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low $R_{DS(ON)}$ and low gate charge. The FDS6699S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology.





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Drain Current – Continuous	(Note 1a)	21	A
	– Pulsed		105	
E_{AS}	Single Pulse Avalanche Energy	(Note 4)	541	mJ
P_D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C
Thermal Characteristics				
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	

Package Marking and Ordering Information

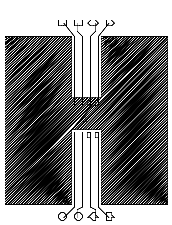
Device Marking	Device	Reel Size	Tape width	Quantity
FDS6699S	FDS6699S	13"	12mm	2500 units

Electrical Characteristics T_A = 25°C unless otherwise noted

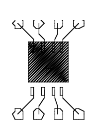
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25°C		28		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			500	μA
I_{GSS}	Gate–Body Leakage	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 1 mA	1	1.4	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25°C		–3.2		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = 10 V, I_D = 21 A V_{GS} = 4.5 V, I_D = 19 A V_{GS}=10 V, I_D =21 A, T_J=150°C		3.0 3.6 4.6	3.6 4.5 5.6	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 21 A		100		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz		3610	4800	pF
C_{oss}	Output Capacitance			1080	1435	pF
C_{rss}	Reverse Transfer Capacitance			340	680	pF
R_G	Gate Resistance	V_{GS} = 15 mV, f = 1.0 MHz	0.4	1.8	3.1	Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = 15 V, I_D = 1 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		11	20	ns
t_r	Turn–On Rise Time			12	22	ns
$t_{d(off)}$	Turn–Off Delay Time			73	117	ns
t_f	Turn–Off Fall Time			38	61	ns
$Q_{g(TOT)}$	Total Gate Charge at Vgs = 10V	V_{DD} = 15 V, I_D = 21 A,		65	91	nC
Q_g	Total Gate Charge at Vgs = 5V			35	49	nC
Q_{gs}	Gate–Source Charge			9		nC
Q_{gd}	Gate–Drain Charge			11		nC
Drain–Source Diode Characteristics and Maximum Ratings						
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 3.5 A (Note 2)		0.36	0.7	V
t_{rr}	Diode Reverse Recovery Time	I_F = 21 A, d_{iF}/d_t = 300 A/µs (Note 3)		32		ns
I_{RM}	Diode Reverse Recovery Current			2.2		A
Q_{rr}	Diode Reverse Recovery Charge			35		nC

Notes:

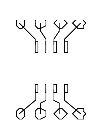
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°/W when mounted on a 1 in^2 pad of 2 oz copper



b) 105°/W when mounted on a .04 in^2 pad of 2 oz copper



c) 125°/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%
3. See "SyncFET Schottky body diode characteristics" below.
4. E_{AS} of 541 mJ is based on starting T_J = 25 °C, L = 3 mH, I_{AS} = 19 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% test at L = 1 mH, I_{AS} = 25 A.

Typical Characteristics

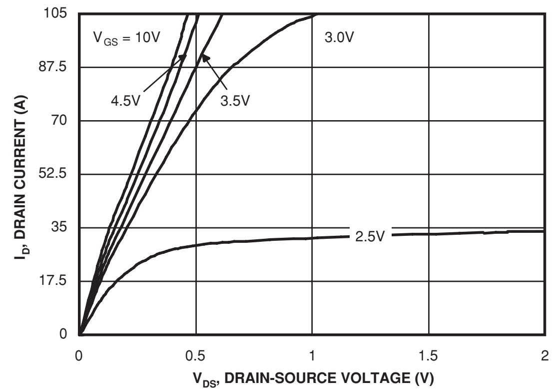


Figure 1. On-Region Characteristics.

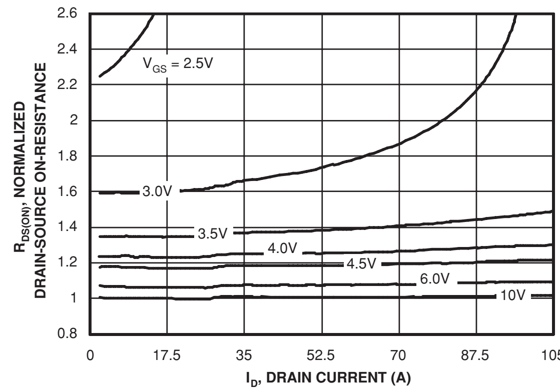


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

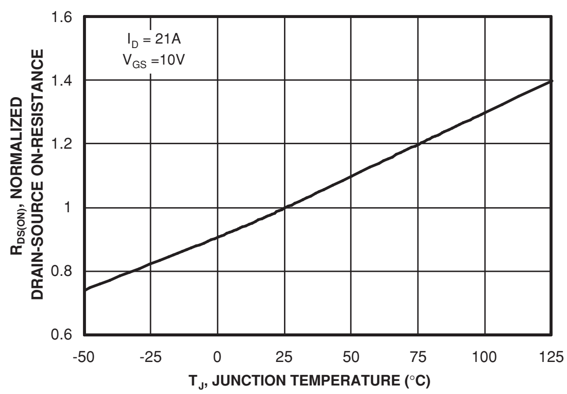


Figure 3. On-Resistance Variation with Temperature.

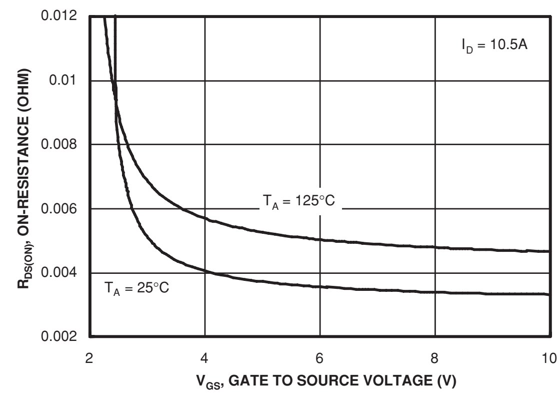


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

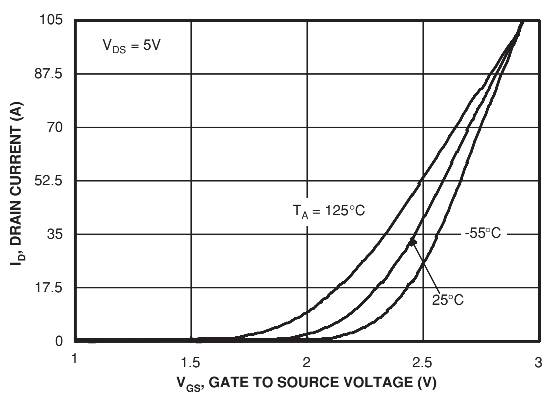


Figure 5. Transfer Characteristics.

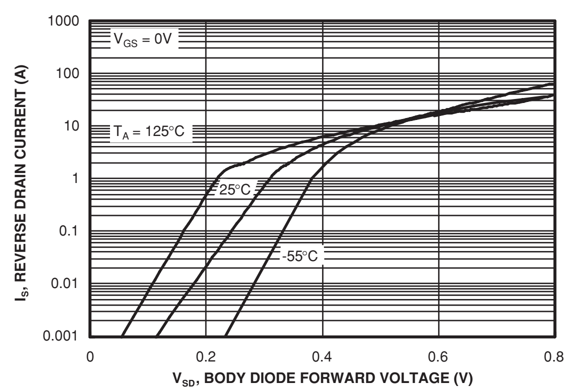


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

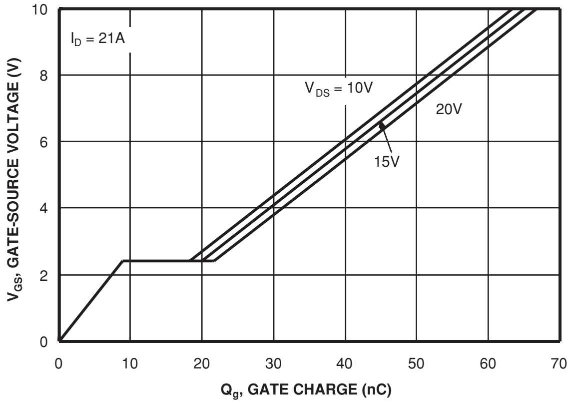


Figure 7. Gate Charge Characteristics.

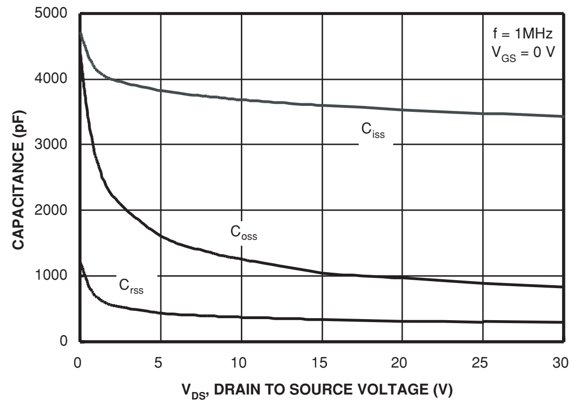


Figure 8. Capacitance Characteristics.

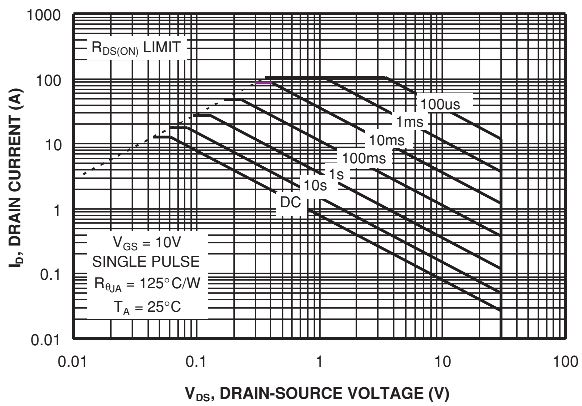


Figure 9. Maximum Safe Operating Area.

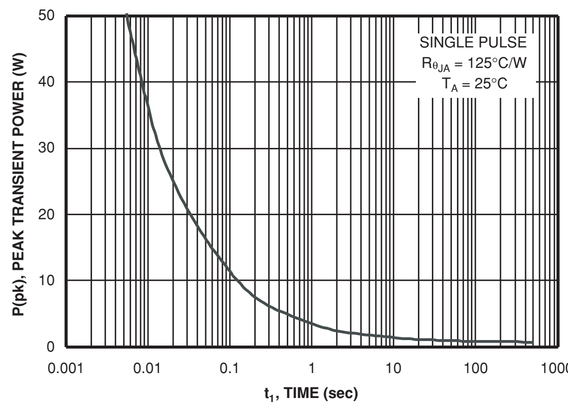


Figure 10. Single Pulse Maximum Power Dissipation.

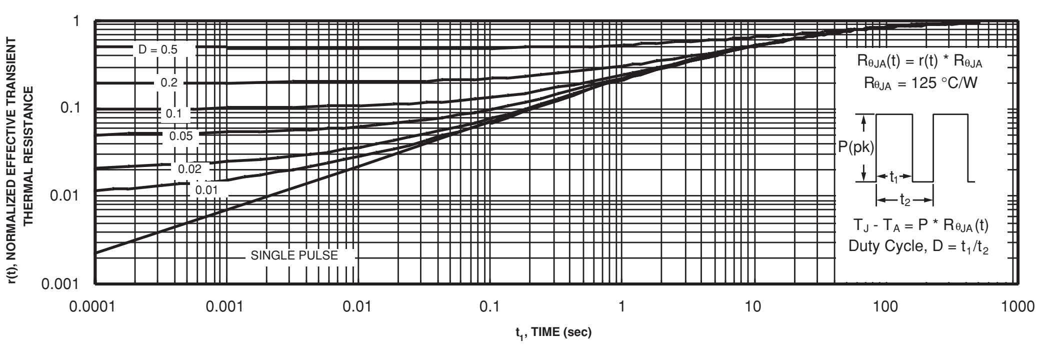


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics (continued)

SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDS6699S.

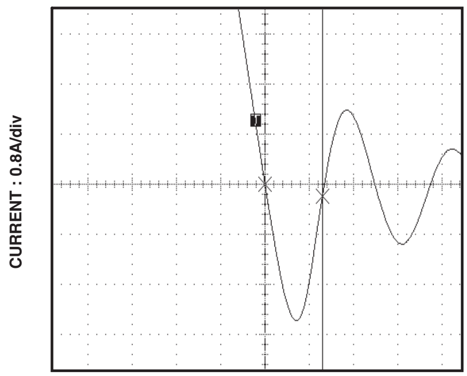


Figure 12. FDS6699S SyncFET body diode reverse recovery characteristic.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

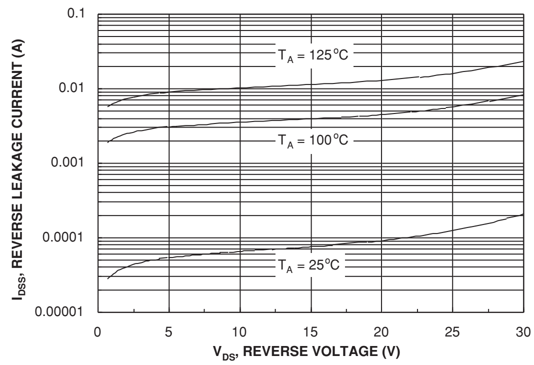


Figure 13. SyncFET body diode reverse leakage versus drain-source voltage and temperature.

PRODUCT STATUS DEFINITIONS
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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